



**BUL138**

## HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- STMicroelectronics PREFERRED SALESTYPE
- NPN TRANSISTOR
- HIGH VOLTAGE CAPABILITY
- LOW SPREAD OF DYNAMIC PARAMETERS
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- VERY HIGH SWITCHING SPEED
- FULLY CHARACTERIZED AT 125°C

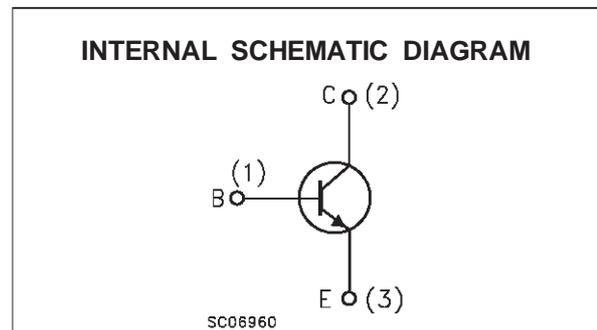
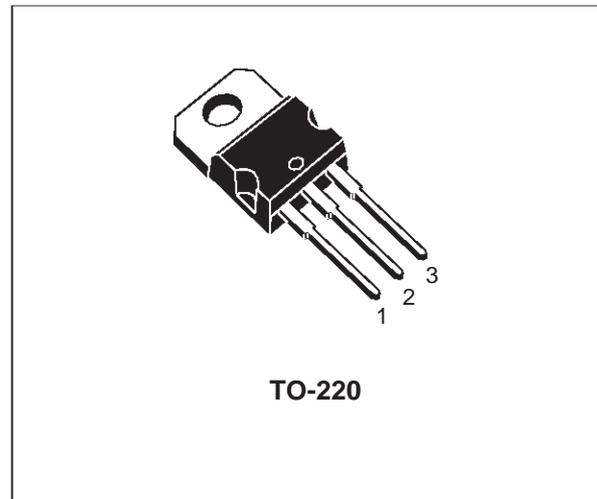
### APPLICATIONS

- ELECTRONIC BALLASTS FOR FLUORESCENT LIGHTING
- FLYBACK AND FORWARD SINGLE TRANSISTOR LOW POWER CONVERTERS

### DESCRIPTION

The BUL138 is manufactured using high voltage Multi Epitaxial Planar technology for high switching speeds and high voltage capability. It uses a Cellular Emitter structure with planar edge termination to enhance switching speeds.

The BUL series is designed for use in lighting applications and low cost switch-mode power supplies.



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-Emitter Voltage ( $V_{BE} = 0$ )	800	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	400	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	9	V
$I_C$	Collector Current	5	A
$I_{CM}$	Collector Peak Current ( $t_p < 5$ ms)	10	A
$I_B$	Base Current	2	A
$I_{BM}$	Base Peak Current ( $t_p < 5$ ms)	4	A
$P_{tot}$	Total Dissipation at $T_c = 25$ °C	80	W
$T_{stg}$	Storage Temperature	-65 to 150	°C
$T_j$	Max. Operating Junction Temperature	150	°C

**THERMAL DATA**

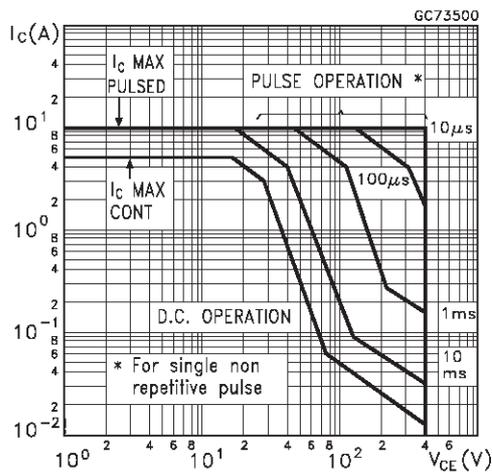
R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	1.56	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	62.5	°C/W

**ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)

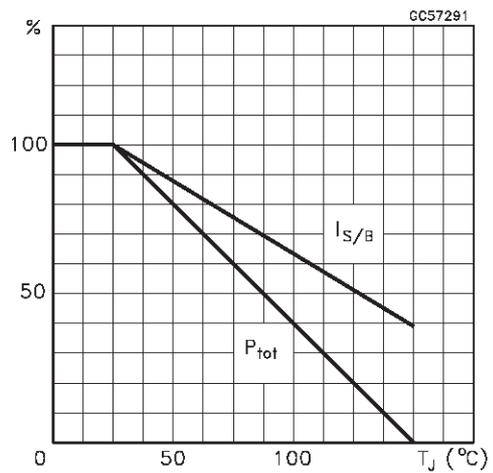
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = 800 V V <sub>CE</sub> = 800 V T <sub>j</sub> = 125 °C			100 500	μA μA
I <sub>CEO</sub>	Collector Cut-off Current (I <sub>B</sub> = 0)	V <sub>CE</sub> = 400 V			250	μA
V <sub>CEO(sus)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 100 mA L = 25 mH	400			V
V <sub>EBO</sub>	Emitter-Base Voltage	I <sub>E</sub> = 10 mA	9			V
V <sub>CE(sat)*</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1 A I <sub>B</sub> = 0.2 A I <sub>C</sub> = 2 A I <sub>B</sub> = 0.4 A I <sub>C</sub> = 3 A I <sub>B</sub> = 0.6 A I <sub>C</sub> = 4 A I <sub>B</sub> = 1 A I <sub>C</sub> = 5 A I <sub>B</sub> = 1 A		0.7	0.5 0.7 1 1	V V V V
V <sub>BE(sat)*</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1 A I <sub>B</sub> = 0.2 A I <sub>C</sub> = 2 A I <sub>B</sub> = 0.4 A I <sub>C</sub> = 3 A I <sub>B</sub> = 0.6 A			1.1 1.3 1.5	V V V
h <sub>FE*</sub>	DC Current Gain	I <sub>C</sub> = 2 A V <sub>CE</sub> = 5 V I <sub>C</sub> = 10 mA V <sub>CE</sub> = 5 V	8 10		40	
t <sub>s</sub>	RESISTIVE LOAD Storage Time	I <sub>C</sub> = 2 A I <sub>B1</sub> = -I <sub>B2</sub> = 0.4 A V <sub>CC</sub> = 250 V	2.4		3.5	μs
t <sub>s</sub> t <sub>f</sub>	INDUCTIVE LOAD Storage Time Fall Time	I <sub>C</sub> = 2 A I <sub>B1</sub> = 0.4 A V <sub>BE(off)</sub> = -5 V R <sub>BB</sub> = 0 Ω V <sub>CL</sub> = 250 V L = 200 μH		0.7 50	1.4 100	μs ns
t <sub>s</sub> t <sub>f</sub>	INDUCTIVE LOAD Storage Time Fall Time	I <sub>C</sub> = 2 A I <sub>B1</sub> = 0.4 A V <sub>BE(off)</sub> = -5V R <sub>BB</sub> = 0 Ω V <sub>CL</sub> = 250 V L = 200 μH T <sub>j</sub> = 125 °C		1 75		μs ns

\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

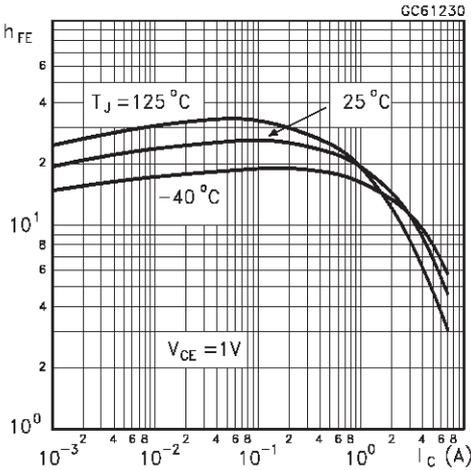
**Safe Operating Areas**



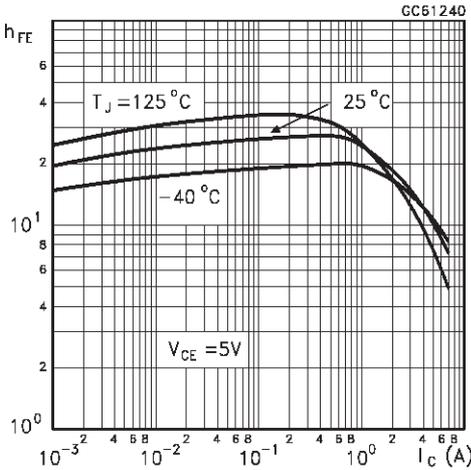
**Derating Curve**



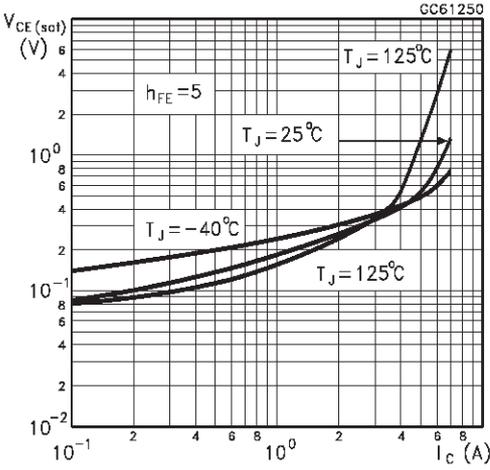
DC Current Gain



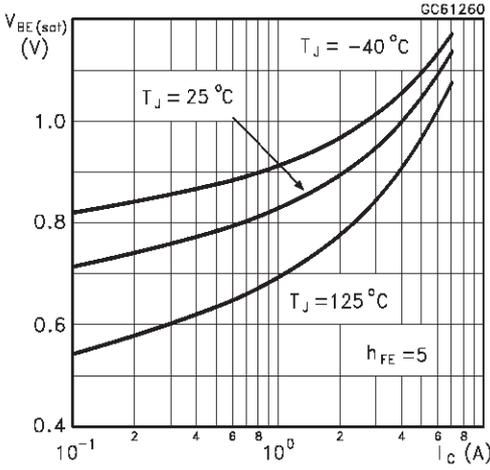
DC Current Gain



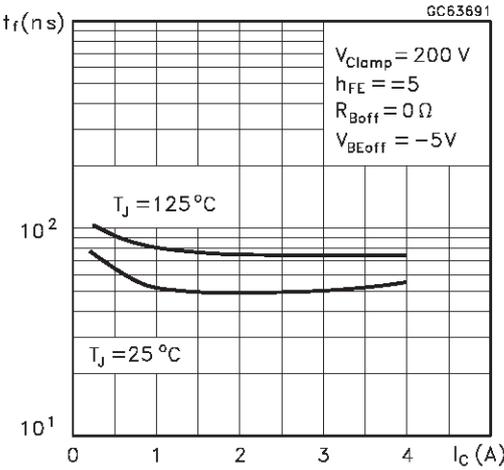
Collector-Emitter Saturation Voltage



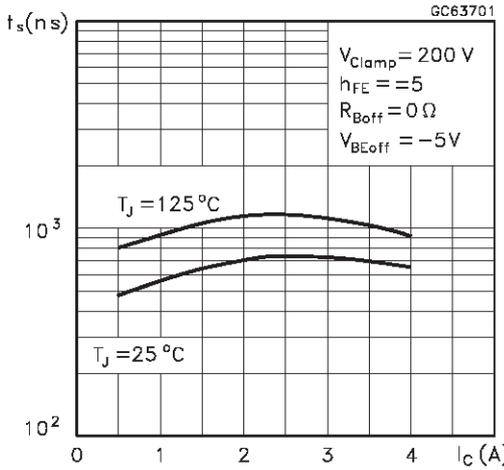
Base-Emitter Saturation Voltage



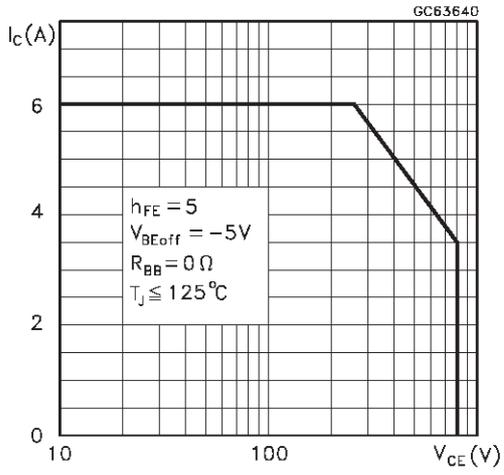
Inductive Fall Time



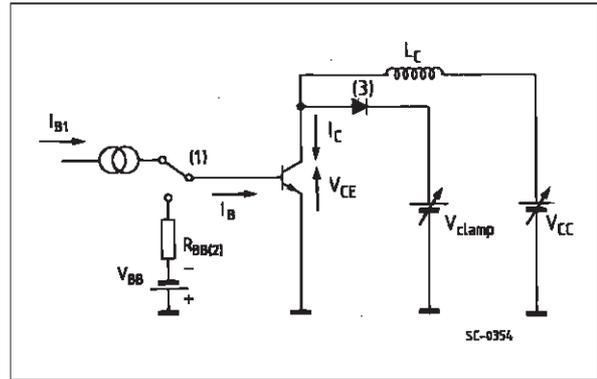
Inductive Storage Time



Reverse Biased SOA



RBSOA and Inductive Load Switching Test Circuits



- 1) Fast electronic switch
- 2) Non-inductive Resistor
- 3) Fast recovery rectifier



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a trademark of STMicroelectronics

© 1999 STMicroelectronics – Printed in Italy – All Rights Reserved

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - France - Germany - Italy - Japan - Korea - Malaysia - Malta - Mexico - Morocco - The Netherlands - Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A.

<http://www.st.com>